

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	990	(438/530).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/27 05:08
L2	707	(438/682).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/27 05:08
L3	260	(438/517).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/27 05:08
L4	92	CABRAL-CYRIL-JR.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/27 05:08
L5	11	KEDZIERSKI-JAKUB-t.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/27 05:09
L6	81	IEONG-MEIKEI .in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/27 05:09
L7	1606	(257/e21.438).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/27 05:09
L8	60	cmos and silicid\$3 with polysilicon with gate with electrode and raised with source and polysilicon with dop\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/27 05:10

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L9	92	CABRAL-CYRIL-JR.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/27 05:10
L10	81	IEONG-MEIKEI .in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/27 05:10
L11	11	KEDZIERSKI-JAKUB-t.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/27 05:10
L12	2	cmos and silicid\$3 with polysilicon with gate with electrode and raised with source and polysilicon with dop\$3 and (L9 or L10 or L11)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/27 05:10
L13	60	cmos and silicid\$3 with polysilicon with gate with electrode and raised with source and polysilicon with dop\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/27 05:10
S1	3739	cmos and silicide and polysilicon with gate with electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/23 17:55
S2	1975	cmos and silicid\$3 same polysilicon with gate with electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/02/28 16:46
S3	1511	cmos and silicid\$3 with polysilicon with gate with electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/02/28 16:46

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S4	79	cmos and silicid\$3 with polysilicon with gate with electrode and raised with source	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/25 16:46
S5	48	cmos and silicid\$3 with polysilicon with gate with electrode and raised with source and polysilicon with dop\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/27 05:10
S6	245	(438/517).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/27 05:08
S7	956	(438/530).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/27 05:08
S8	628	(438/682).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/27 05:08
S9	78	CABRAL-CYRIL-JR.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/27 05:08
S10	62	IEONG-MEIKEI .in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/27 05:09
S11	9	KEDZIERSKI-JAKUB-t.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/27 05:09

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S12	49	cmos and silicid\$3 with polysilicon with gate with electrode and raised with source and polysilicon with dop\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/27 05:10
S13	2	cmos and silicid\$3 with polysilicon with gate with electrode and raised with source and polysilicon with dop\$3 and (S9 or S10 or S11)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/10/27 05:10
S14	5	"6518113"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/02 19:37
S15	7	"6599831"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/02 19:42
S16	506	(438/649).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/25 16:47
S17	26	cmos and silicid\$3 with polysilicon with gate with electrode and raised with source and polysilicon with dop\$3 and soi	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/02 21:40
S18	2	cmos and silicid\$3 with polysilicon with gate with electrode and raised with source and polysilicon with dop\$3 and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/25 16:50
S19	8	((("6,544,829") or ("5,100,173") or ("5,534,837") or ("5,458,678")).PN. or ((2003/096491) or (2003/092249) or (2002/053711)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/25 16:47